L Number	Hits	Search Text	DB	Time stamp
1	1083	(rh with ir) and (electrode adj (layer or film))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/31 09:31
2	97	(rh with ir) with (electrode adj (layer or film))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/31 09:39
3	4	(rh with ir) with (electrode adj (layer or film)) with laminat$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/31 09:44
4	2	(rhodium with iridium) with (electrode adj (layer or film)) with laminat$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/31 09:45
5	10	(rhodium with iridium) with (electrode) with laminat$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/31 09:51
6	26	(rh with ir) with (electrode) with laminat$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/31 10:18
7	77	((rh or rhodium) with (ir or iridium)) with (condutor or metal) with laminat$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/31 10:20
8	1	(ir or iridium) adj laminat$ adj (rh or rhodium)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/31 10:21
9	195	(ir or iridium) with laminat$ with (rh or rhodium)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/31 10:22
10	35	(ir or iridium) with laminat$ with (rh or rhodium) with electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/31 10:56
11	167	thickness with (rh or rhodium) with electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/31 10:56
12	0	(thickness adj (rh or rhodium)) with (ir or iridium) with electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/31 10:57
13	3	(thickness adj (rh or rhodium)) with electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/31 11:45
14	0	(ir or iridium) with (rh or rhodium) with (electrode adj annealed)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/31 11:47

15	0	(ir or iridium) with (rh or rhodium) with (electrode adj anneal$)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/31 11:47
16	8	(ir or iridium) with (rh or rhodium) with electrode with anneal$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/31 11:51
17	57	((ir or iridium) with (rh or rhodium) with electrode) same anneal$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/31 12:13
18	26	(((ir or iridium) adj (rh or rhodium)) with electrode) same anneal$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/31 13:25
19	497	257/13.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/31 14:14
20	1072	257/79.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/31 14:15
21	597	257/80.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/31 14:16
22	953	257/94.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/31 14:16
23	695	257/184.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/31 14:17
24	1304	257/431.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/31 14:17
25	1270	257/432.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/31 14:18
26	266	257/86.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/31 14:18
27	1596	257/103.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/31 14:18
28	550	257/436.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/31 14:20

29	3	257/13.ccls. and ((rh or rhodium) with (ir or iridium))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/31 14:14
30	19	257/79.ccls. and ((rh or rhodium) with (ir or iridium))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/31 14:15
31	5	257/80.ccls. and ((rh or rhodium) with (ir or iridium))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/31 14:16
32	11	257/94.ccls. and ((rh or rhodium) with (ir or iridium))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/31 14:16
33	2	257/184.ccls. and ((rh or rhodium) with (ir or iridium))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/31 14:17
34	8	257/431.ccls. and ((rh or rhodium) with (ir or iridium))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/31 14:17
35	4	257/432.ccls. and ((rh or rhodium) with (ir or iridium))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/31 14:18
36	1	257/86.ccls. and ((rh or rhodium) with (ir or iridium))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/31 14:18
37	43	257/103.ccls. and ((rh or rhodium) with (ir or iridium))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/31 14:18
38	3	257/436.ccls. and ((rh or rhodium) with (ir or iridium))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/31 14:20
40	616	257/$.ccls. and ((rh or rhodium) with (ir or iridium) with electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/31 14:21
41	100	257/$.ccls. and ((rh or rhodium) with (ir or iridium) with electrode with nitride)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/31 14:28
42	22	257/$.ccls. and ((rh or rhodium) with (ir or iridium) with electrode with nitride) and light	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/31 14:28
-	16	(nitride adj semiconductor) and (electrode with rhodium with iridium)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/16 12:27

-	0	sonobe.inv	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/16 12:28
-	1	sonobe.inv. and (electrode with rhodium with iridium)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/16 12:34
-	1	sonobe.inv. and (electrode with rh with ir)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/16 12:29
-	1	sonobe.inv. and (rh with ir) and (nitride adj semiconductor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 17:43
-	16	sonobe.inv. and (nitride adj semiconductor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/16 12:31
-	2	sonobe.inv. and (nitride adj semiconductor) and rhodium	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/16 12:32
-	3	sonobe.inv. and (nitride adj semiconductor) and rh	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/16 12:33
-	1	sonobe.inv. and (nitride adj semiconductor) and iridium	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/16 12:33
-	1	sonobe.inv. and (nitride adj semiconductor) and ir	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/16 12:33
-	2	sonobe.inv. and (rhodium with iridium)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/16 12:34
-	1136	(rh with ir) with electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 20:12
-	495	((rh with ir) with electrode) and nitride	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 23:32
-	4	((rh with ir) with (p adj electrode)) and nitride	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 19:07
-	5	((rh with ir) with (p adj side adj electrode)) and nitride	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 20:08

-	0	20030209717.pn. and (temperature or anneal)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 20:08
-	1	20030209717.pn. and (temperature or anneal$)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 21:42
-	199	((rh with ir) with electrode) and laminat$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 20:13
-	26	((rh with ir) with electrode) with laminat$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 20:20
-	1	((rh with ir) with (laminat$ adj electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 20:22
-	1	((rhodium with iridium) with (laminat$ adj electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 20:23
-	0	((rhodium with iridium) with (two adj layer adj electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 20:23
-	0	((rhodium with iridium) same (two adj layer adj electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 20:24
-	6	((rhodium with iridium) and (two adj layer adj electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 20:25
-	0	((rhodium with iridium) and (dual adj layer adj electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 20:25
-	8	((rhodium with iridium) and (double adj layer adj electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 20:28
-	8	((rhodium with iridium) and (multiple adj layer adj electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 20:30
-	13	((rhodium with iridium) and (multi adj layer adj electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 20:35
-	183	((rhodium with iridium) and (plurality adj electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 20:35

-	2	((rhodium with iridium) with (plurality adj electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 20:36
-	0	((rhodium with iridium) with (multiple adj electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 20:37
-	2	((rhodium with iridium) with (multi adj electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 20:37
-	0	((rhodium with iridium) with (plural adj electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 20:37
-	0	((rhodium with iridium) with (dual adj electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 20:38
-	0	((rhodium with iridium) with (double adj electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 20:38
-	4	((rhodium with iridium) with (two adj electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 20:40
-	10	((rhodium with iridium) with (laminat$ with electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 20:45
-	26	((rh with ir) with (laminat$ with electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 21:17
-	169	laminat$ with ir with rh	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 21:03
-	26	laminat$ with ir with rh with electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 21:03
-	10	laminat$ with iridium with rhodium with electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 21:07
-	8	(laminat$ with (ir adj rh)) with electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 21:09
-	2	ir adj rh adj electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 21:12

-	0	iriudium adj rhodium adj electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 21:11
-	1	iridium adj rhodium adj electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 21:11
-	0	iridium adj rhodium adj terminal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 21:11
-	0	ir adj rh adj terminal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 21:12
-	10	(two adj layered) with (ir or iridium) with (rh or rhodium)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 21:13
-	93	(nitride adj semiconductor) with (laminat$ with electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 21:18
-	1	(nitride adj semiconductor) with (laminat$ with electrode) with (ir or iridium) with (rh or rhodium)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 21:19
-	0	(nitride adj semiconductor) with (two adj layered) with (ir or iridium) with (rh or rhodium)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 21:19
-	0	(nitride adj semiconductor) with (dual adj layered) with (ir or iridium) with (rh or rhodium)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 21:19
-	1	(nitride adj semiconductor) with (two adj layer$) with (ir or iridium) with (rh or rhodium)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 21:20
-	0	(nitride adj semiconductor) with (dual adj layer$) with (ir or iridium) with (rh or rhodium)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 21:20
-	0	(nitride adj semiconductor) with (double adj layer$) with (ir or iridium) with (rh or rhodium)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 21:21
-	4	(nitride adj semiconductor) and (double adj layer$) and ((ir or iridium) with (rh or rhodium))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 21:30
-	0	(nitride adj semiconductor) and (ir adj rh adj double adj layer$)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 21:31

-	0	(nitride adj semiconductor) and (ir adj rh adj multi adj layer$)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 21:32
-	0	(nitride adj semiconductor) and (ir adj rh adj multiple adj layer$)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 21:33
-	0	(nitride adj semiconductor) and (ir adj rh adj dual adj layer$)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 21:33
-	0	(nitride adj semiconductor) and (ir adj rh adj two adj layer$)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 21:33
-	0	(nitride adj semiconductor) and (ir adj rh adj multilayer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 21:34
-	0	(nitride adj semiconductor) and ((ir adj rh) with multilayer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 21:34
-	0	(nitride adj semiconductor) and ((ir adj rh) same multilayer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 21:34
-	0	(nitride adj semiconductor) and ((ir adj rh) and multilayer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 21:35
-	0	(nitride adj semiconductor) and ((ir adj rh) and multilayer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 21:35
-	97	(nitride) and ((ir adj rh) and multilayer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 21:35
-	11	(nitride) and ((ir adj rh) with multilayer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 21:40
-	0	(nitride) and ((ir adj rh) with (two adj layered))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 21:41
-	2	5990500.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 21:42
-	1	5990500.pn. and ir and rh	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 21:47

-	862	stacked adj electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 21:47
-	9	(stacked adj electrode) and nitride and (ir with rh)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 21:52
-	83	(electrode adj stack) and nitride and (ir with rh)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 22:03
-	18	(composite adj electrode) and nitride and (ir with rh)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 22:07
-	3	(electrode) and nitride and (ir near formed near rh)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 22:09
-	16	(electrode) and nitride and (ir adj rh adj alloy)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 22:14
-	9	(compound adj electrode) and nitride and (ir near rh)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 22:15
-	0	((rh with ir) with electrode with anneal) and nitride	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 23:32
-	3	((rh with ir) with electrode with anneal$) and nitride	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/29 23:34
-	11	((rh with ir) with electrode with temperature) and nitride	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/31 09:30